

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
9 June 2005 (09.06.2005)

PCT

(10) International Publication Number
WO 2005/052893 A1

(51) International Patent Classification⁷: **G09F 9/00,**
H05B 33/10, G02F 1/1333

Yuugo [JP/JP]; c/o SEMICONDUCTOR ENERGY LAB-
ORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa,
2430036 (JP).

(21) International Application Number:
PCT/JP2004/017537

(81) Designated States (*unless otherwise indicated, for every kind of regional protection available*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(22) International Filing Date:
18 November 2004 (18.11.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2003-399926 28 November 2003 (28.11.2003) JP

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

(71) Applicant (*for all designated States except US*): SEMI-
CONDUCTOR ENERGY LABORATORY CO., LTD.
[JP/JP]; 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP).

(72) Inventors; and

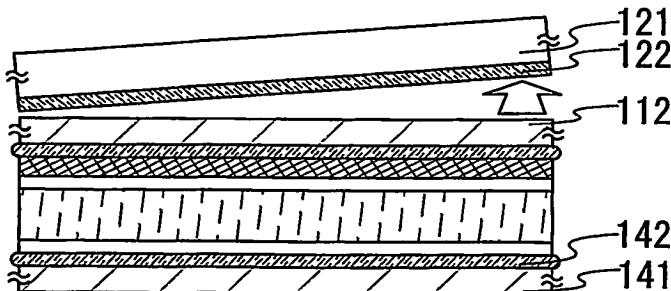
(75) Inventors/Applicants (*for US only*): YAMASHITA,
Akio [JP/JP]; c/o SEMICONDUCTOR ENERGY LABO-
RATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa,
2430036 (JP). FUKUMOTO, Yumiko [JP/JP]; c/o SEMI-
CONDUCTOR ENERGY LABORATORY CO., LTD.,
398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP). GOTO,

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: METHOD OF MANUFACTURING DISPLAY DEVICE



(57) Abstract: To provide a method of manufacturing a display device having an excellent impact resistance property with high yield, in particular, a method of manufacturing a display device having an optical film that is formed using a plastic substrate. The method of manufacturing a display device includes the steps of: laminating a metal film, an oxide film, and an optical filter on a first substrate; separating the optical filter from the first substrate; attaching the optical filter to a second substrate; forming a layer including a pixel on a third substrate; and attaching the layer including the pixel to the optical filter.